

IRLL3303TRPBF-VB Datasheet N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	30
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.019
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.021
I _D (A)	7
Configuration	Single

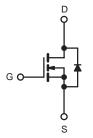
FEATURES

- Trench Power MOSFET
- 100 % R_q and UIS Tested









N-Channel MOSFET

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unles	s otherwise noted	d)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	30	
Gate-Source Voltage		V_{GS}	± 20	V
Osalis as Bais Osasal	T _C = 25 °C	· I _D	7	
Continuous Drain Current	T _C = 125 °C		4.5	
Continuous Source Current (Diode Conduction)		I _S	5	А
Pulsed Drain Current ^a		I _{DM}	31	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	10	
Single Pulse Avalanche Energy	L = 0.1 mm	E _{AS}	5	mJ
Mariana Damar Dissipation?	T _C = 25 °C	В	4	W
Maximum Power Dissipation ^a	T _C = 125 °C	P_{D}	1.3	·
Operating Junction and Storage Temperature	re Range	T _J , T _{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^b	R_{thJA}	110	°CAM
Junction-to-Foot (Drain)		R_{thJF}	38	°C/W

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.



PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static					l .		<u> </u>
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		30	-	-	W
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	0.5	-	1.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	=	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 30 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 30 V, T _J = 125 °C	-	-	50	μΑ
		$V_{GS} = 0 V$	V _{DS} = 30 V, T _J = 175 °C	-	-	150	V nA
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α
Drain-Source On-State Resistance ^a		V _{GS} = 10 V	I _D = 6 A	=	0.019	-	Ω
	D	V _{GS} = 4.5 V	I _D = 4.9 A	=	0.021	-	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 6 A, T _J = 125 °C	-	0.054	-	
		V _{GS} = 10 V	I _D = 6 A, T _J = 175 °C	=	0.064	-	
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 5 A		-	21	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	295	-	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 15 \text{ V, f} = 1 \text{ MHz}$	=	67	-	pF
Reverse Transfer Capacitance	C _{rss}			-	25	-	
Total Gate Charge ^c	Qg			-	6	-	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 15 \text{ V}, I_{D} = 6 \text{ A}$	-	1.2	-	nC
Gate-Drain Charge ^c	Q _{gd}	1		-	1	-	
Gate Resistance	R_g	f = 1 MHz		3.0	6.65	11	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	6	9	
Rise Time ^c	t _r	$V_{DD} = 15 \text{ V}, R_{I} = 2.5 \Omega$		-	12	18	1
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 6 A$,	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	13	20	ns
Fall Time ^c	t _f	1		-	8	12	1
Source-Drain Diode Ratings and Chara	acteristics ^b	•					<u> </u>
Pulsed Current ^a	I _{SM}			-	-	31	Α
Forward Voltage	V _{SD}	lc =	= 3 A, V _{GS} = 0 V	_	0.8	1.1	V

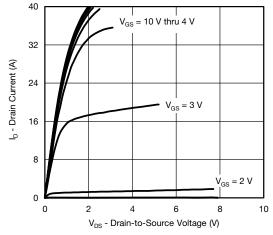
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

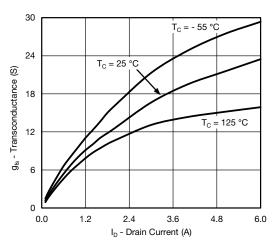
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



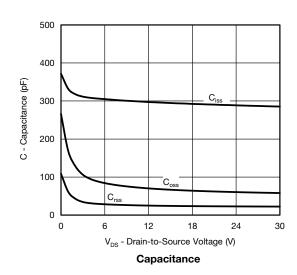
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

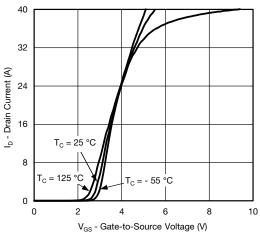




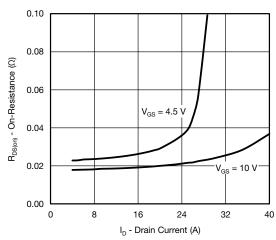


Transconductance

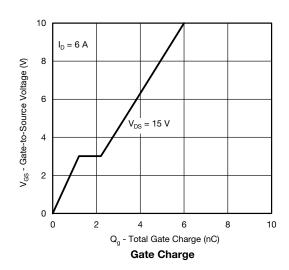




Transfer Characteristics

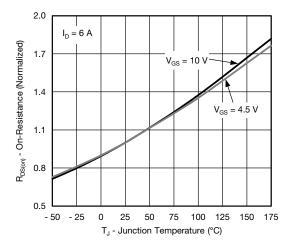


On-Resistance vs. Drain Current

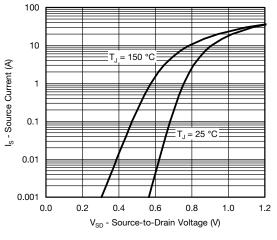




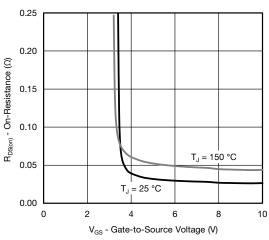
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



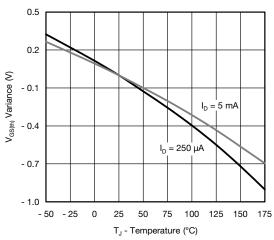
On-Resistance vs. Junction Temperature



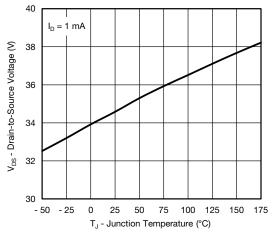
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



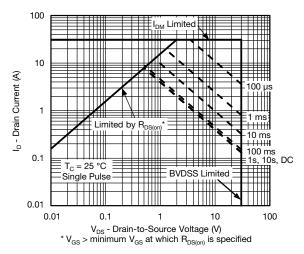
Threshold Voltage



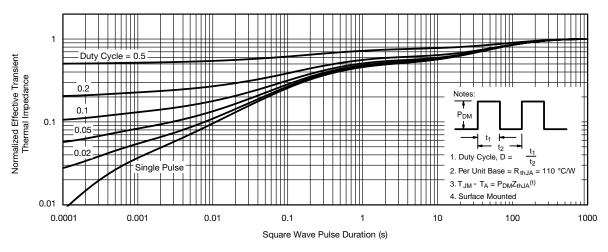
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



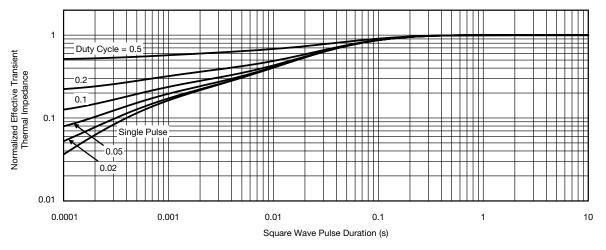
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



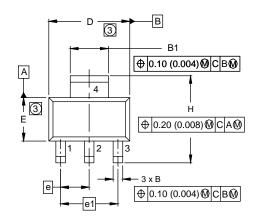
Normalized Thermal Transient Impedance, Junction-to-Foot

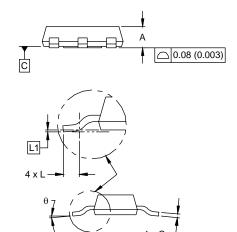
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



SOT-223 (HIGH VOLTAGE)





DIM.	MILLII	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.		
Α	1.55	1.80	0.061	0.071		
В	0.65	0.85	0.026	0.033		
B1	2.95	3.15	0.116	0.124		
С	0.25	0.35	0.010	0.014		
D	6.30	6.70	0.248	0.264		
E	3.30	3.70	0.130	0.146		
е	2.30 BSC		0.0905 BSC			
e1	4.60	4.60 BSC		BSC		
Н	6.71	7.29	0.264	0.287		
L	0.91	-	0.036	-		
L1	0.061 BSC		0.0024	BSC		
θ	-	10'	-	10'		

ECN: S-82109-Rev. A, 15-Sep-08

DWG: 5969

Notes

- 1. Dimensioning and tolerancing per ASME Y14.5M-1994.
- 2. Dimensions are shown in millimeters (inches).
- 3. Dimension do not include mold flash.
- 4. Outline conforms to JEDEC outline TO-261AA.



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